Schottky Diode

|		
V_{RRM}	$=$	$200\,V$
I_{FAV}	$=2x$	$10\,A$
V_F	$=$	$0.75\,V$

High Performance Schottky Diode
Low Loss and Soft Recovery
Common Cathode

Part number

DSA20C200PB
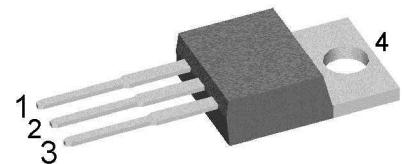
Backside: cathode
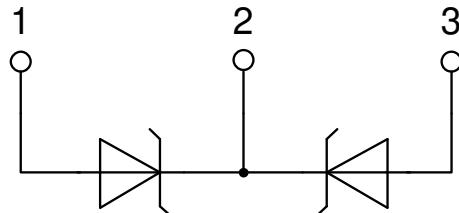
Features / Advantages:

- Very low Vf
- Extremely low switching losses
- Low Irm values
- Improved thermal behaviour
- High reliability circuit operation
- Low voltage peaks for reduced protection circuits
- Low noise switching

Applications:

- Rectifiers in switch mode power supplies (SMPS)
- Free wheeling diode in low voltage converters

Package: TO-220

- Industry standard outline
- RoHS compliant
- Epoxy meets UL 94V-0

Disclaimer Notice

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Symbol	Definition	Conditions		min.	typ.	max.	Unit
V_{RSM}	max. non-repetitive reverse blocking voltage		T_{VJ} = 25°C			200	V
V_{RRM}	max. repetitive reverse blocking voltage		T_{VJ} = 25°C			200	V
I_R	reverse current, drain current	V_R = 200 V	T_{VJ} = 25°C			200	µA
		V_R = 200 V	T_{VJ} = 125°C			2	mA
V_F	forward voltage drop	I_F = 10 A	T_{VJ} = 25°C			0.91	V
		I_F = 20 A				1.06	V
		I_F = 10 A	T_{VJ} = 125°C			0.75	V
		I_F = 20 A				0.90	V
I_{FAV}	average forward current	T_C = 155°C	T_{VJ} = 175°C			10	A
		rectangular d = 0.5					
V_{F0}	threshold voltage ⎫		T_{VJ} = 175°C			0.53	V
r_F	slope resistance ⎭ for power loss calculation only					14	mΩ
R_{thJC}	thermal resistance junction to case					2.4	K/W
R_{thCH}	thermal resistance case to heatsink				0.5		K/W
P_{tot}	total power dissipation		T_C = 25°C			65	W
I_{FSM}	max. forward surge current	t = 10 ms; (50 Hz), sine; V_R = 0 V	T_{VJ} = 45°C			220	A
C_J	junction capacitance	V_R = 24 V f = 1 MHz	T_{VJ} = 25°C		44		pF

Package	TO-220		Ratings			
Symbol	**Definition**	**Conditions**	**min.**	**typ.**	**max.**	**Unit**
I_{RMS}	*RMS current*	per terminal [1]			35	A
T_{VJ}	*virtual junction temperature*		-55		175	°C
T_{op}	*operation temperature*		-55		150	°C
T_{stg}	*storage temperature*		-55		150	°C
Weight				2		g
M_D	*mounting torque*		0.4		0.6	Nm
F_C	*mounting force with clip*		20		60	N

Product Marking

Part Number → XXXXXX
Logo → IXYS   yywwZ
Date Code →
Lot # → 123456
Location →
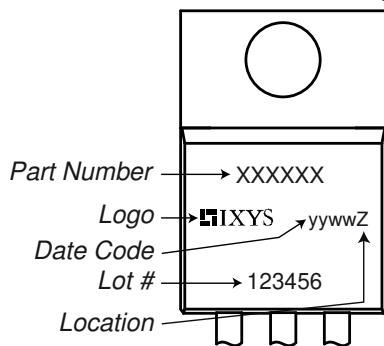
Part description

D = Diode
S = Schottky Diode
A = low VF
20 = Current Rating [A]
C = Common Cathode
200 = Reverse Voltage [V]
PB = TO-220AB (3)

Ordering	Ordering Number	Marking on Product	Delivery Mode	Quantity	Code No.
Standard	DSA20C200PB	DSA20C200PB	Tube	50	523035

Equivalent Circuits for Simulation   ** on die level* $T_{VJ} = 175$°C
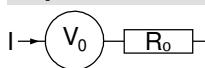
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$V_{0 max}$	*threshold voltage*	0.53	V
$R_{0 max}$	*slope resistance **	10.8	mΩ

Outlines   TO-220

----- = supplier option
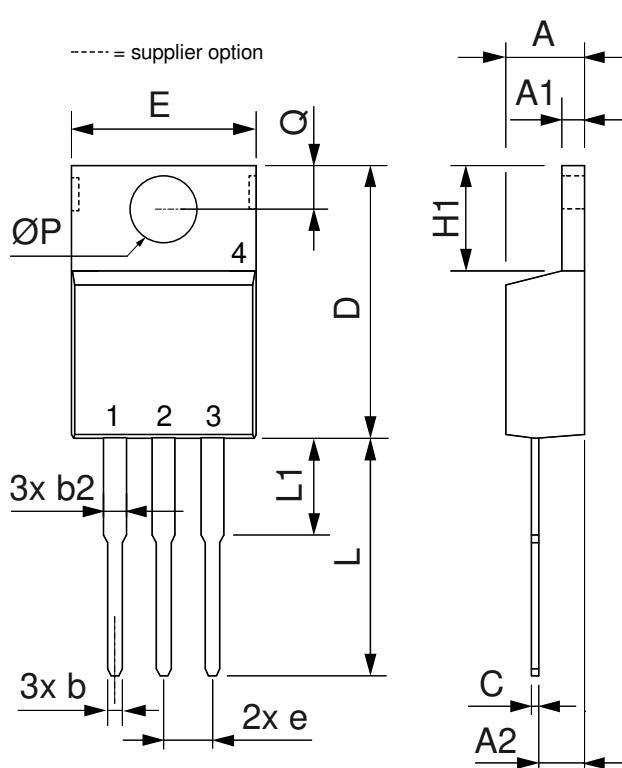
Dim.	Millimeter		Inches	
	Min.	Max.	Min.	Max.
A	4.32	4.82	0.170	0.190
A1	1.14	1.39	0.045	0.055
A2	2.29	2.79	0.090	0.110
b	0.64	1.01	0.025	0.040
b2	1.15	1.65	0.045	0.065
C	0.35	0.56	0.014	0.022
D	14.73	16.00	0.580	0.630
E	9.91	10.66	0.390	0.420
e	2.54	BSC	0.100	BSC
H1	5.85	6.85	0.230	0.270
L	12.70	13.97	0.500	0.550
L1	2.79	5.84	0.110	0.230
ØP	3.54	4.08	0.139	0.161
Q	2.54	3.18	0.100	0.125

IXYS reserves the right to change limits, conditions and dimensions.   Data according to IEC 60747and per semiconductor unless otherwise specified   20200128d

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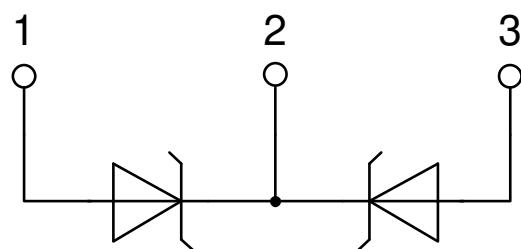
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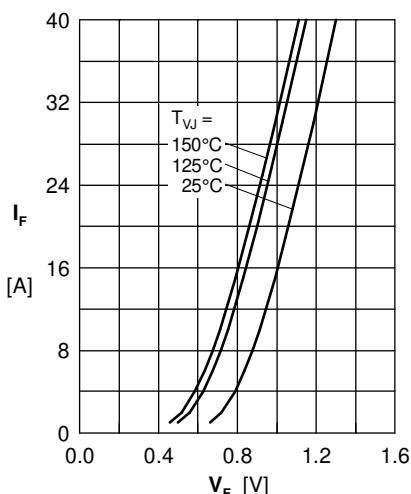
Fig. 1 Maximum forward voltage drop characteristics
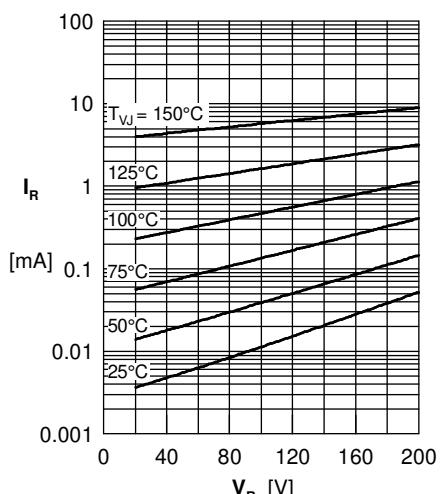
Fig. 2 Typ. reverse current I_R vs. reverse voltage V_R
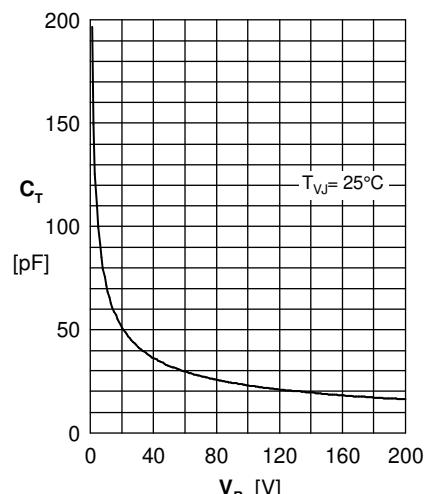
Fig. 3 Typ. junction capacitance C_T versus reverse voltage V_R
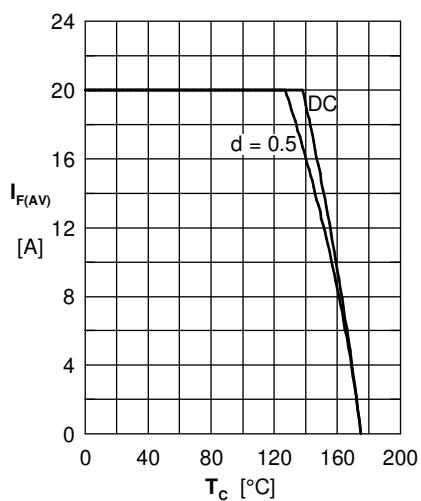
Fig. 4 Avg: forward current $I_{F(AV)}$ vs. case temperature T_C
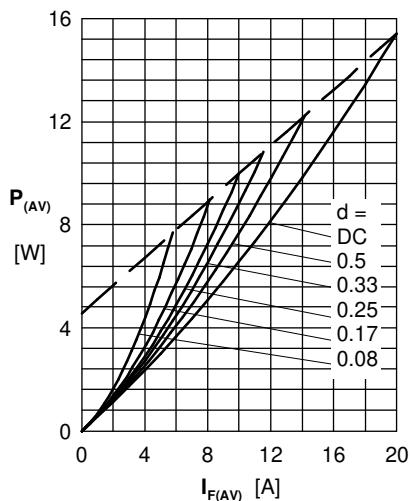
Fig. 5 Forward power loss characteristics
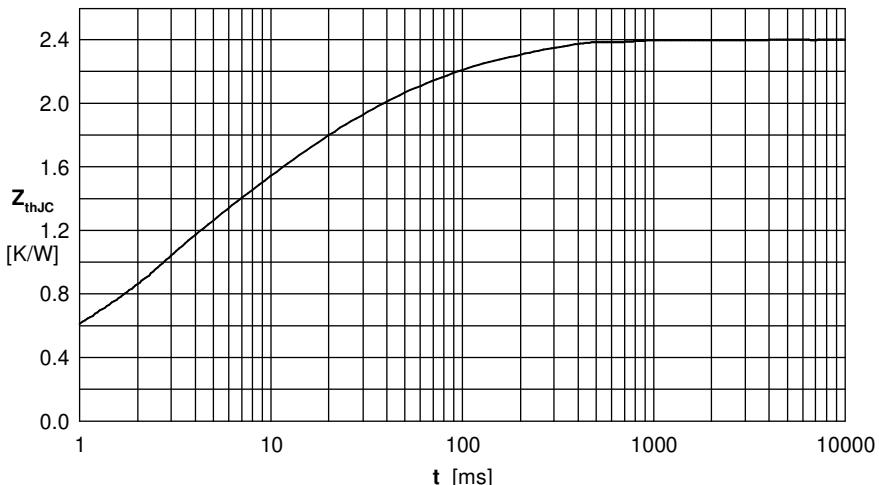
Fig. 6 Transient thermal impedance junction to case

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